



Nanotechnology & Microsystems Lab Overview

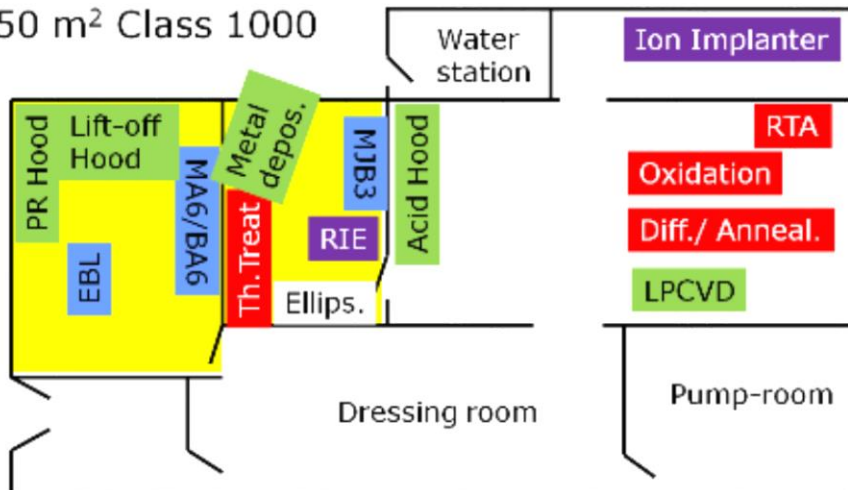
Our Aim is to

- Promote Semiconductors processing and manufacturing technologies
- Support industry with high added value products and production processes
- Support industry in realizing their technology roadmap and participate in European and globally funded Research projects
- Develop human potential by education and training activities in cutting edge technologies

What we offer

- Production of cutting edge technology prototypes
- Process troubleshooting, improvement and new process development based on customer requirements
- Full support of process transfer to production site
- Electrical characterization of semiconductor devices
- Structural characterization and microscopy
- Utilize existing channels for incorporating research and development activities in EU-funded projects

250 m² Class 1000



Infrastructure

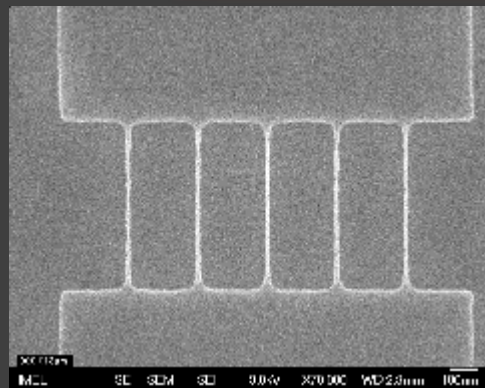
- ISO 6 / ISO 5
- 250 m² – 70m² expansion scheduled for 1H23
- Fully Equipped CMOS Compatible Line
- ISO 8 Satellite labs supporting non CMOS compatible processes
- **Satellite labs of Plasma Etching, CVD, MBE, Organic electronics, characterization.....**



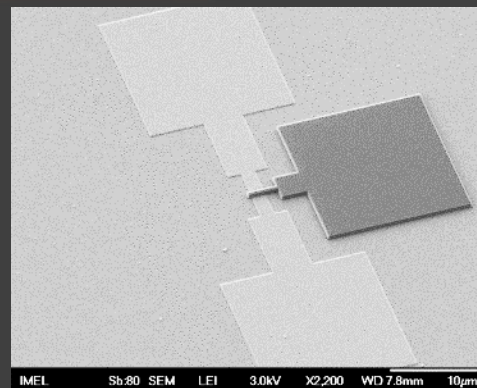
Nanotechnology & Microsystems Lab Processes & Characterization

Processes

- Optical Mask Aligner (SUSS Microtech with back side alignment)
- Electron Beam Patern Generator (RAITH EBPG 5000 plus)
- Dry (plasma) Etcher (RIE, ICP)
- Ion Implanter Eaton NV-3204
- Thermal Processes (Atmospheric, LPCVD, RTA, RTP)
- Electrical Characterization:
 - RF Characterization
 - 2-port Vector Network Analyzer with Frequency Range 40 MHz-40 GHz
 - DC Current – Voltage Characterization
 - DC Characterization LCR Meter
 - DC / AC Pulse Generator
 - Variable Temperature Wafer Prober
- Several Characterization Techniques and supporting satellite labs



13nm Nanowire MOSFET



Si FinFET 30nm



Nanotechnology & Microsystems Lab Future Expansion



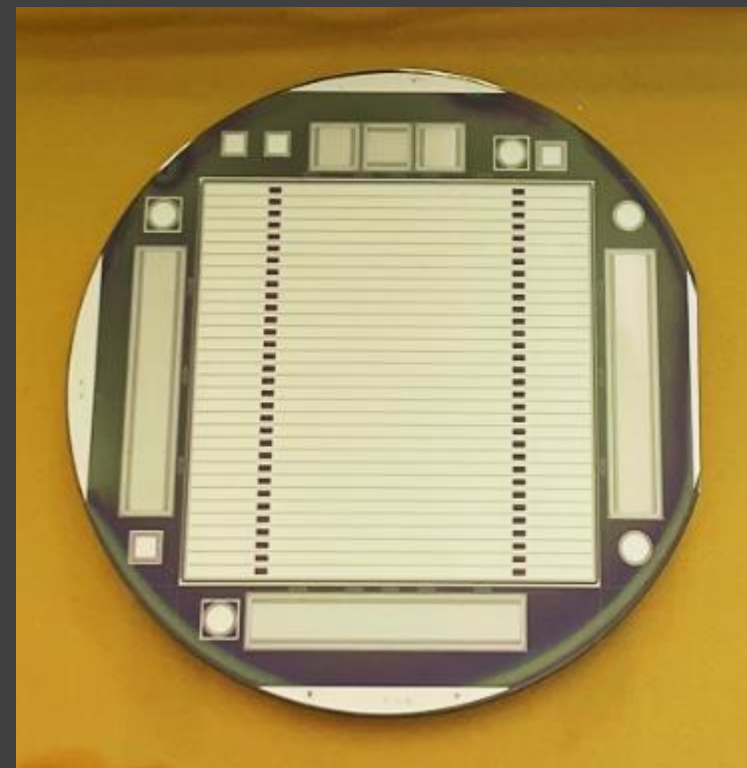
- 75m² of Clean Room Class 100 will be added within the 1st Half of 2023
- 1 Atomic Layer Etching Tool with RIE / ICP Capabilities
- 1 e-Gun Evaporation tool for metals with capability of depositing alloys
- 1 Thermal evaporator tool with capability of depositing organic layers
- All systems will be operational in 2nd Half of 2023

- The project is funded by the Hellenic Foundation for Research and Innovation (ELIDEK) under contract number 34666/17.3.21

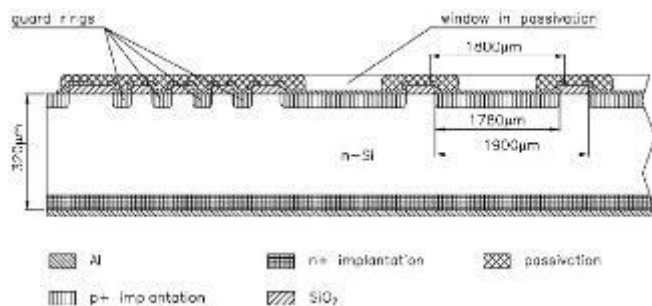


Nanotechnology & Microsystems Lab

Achievements: Si Sensors for the CMS Preshower Detector



- NML worked 20 years ago on the development of the prototypes
- Designed especially for the preshower detector to separate the photons from the neutral pions (γ/π^0)
- Silicon based sensors are fast and have a linear response even in harsh environments
- Some characteristics:
 - Wafer size: 4'', F-Z
 - Wafer thickness: $320\mu\text{m} \pm 2\mu\text{m}$ (optimal for low leakage currents)
 - Resistivity: 3 – 4k Ω .cm
 - Number of strips: 32
 - Total area: 63 \times 63cm²



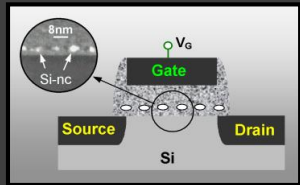


Nanotechnology & Microsystems Lab Achievements: Nanoelectronics

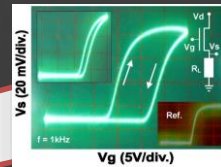
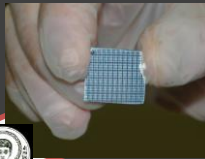
Si NanoCrystal Memories by Low-Energy
Ion-Beam-Synthesis (A Long Story)

Development of Non-Volatile Memories

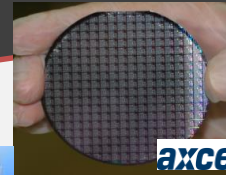
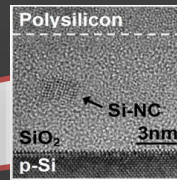
- From Materials to Devices
- Technology Transfer to Industry



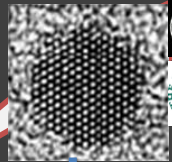
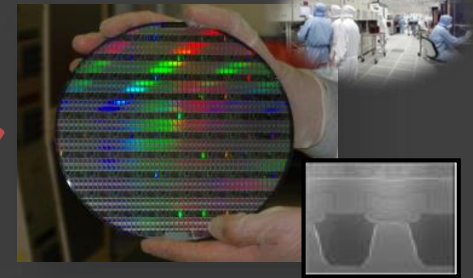
1996-2000



2001-2003



2004-2006



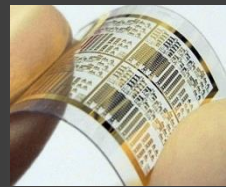
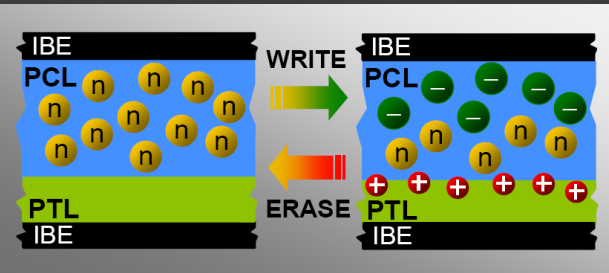
Si-NCs 2D-arrays
in thin SiO₂

Laboratory Si-NCMs
(2 μm n-MOS Technology)

Si-NCM Manufacturing
(STMicroelectronics 0.15 μm
Flash Memory Technology)

Towards Reprogrammable Non-Volatile Organic Memories

2008: Introduction of the Concept of
Non-Volatile Proton Organic Memory





Nanotechnology & Microsystems Lab

What we can offer to CERN

- Prototype development of sensors, micro / nano systems, devices (electronics / opto-electronics)
- Small production of custom designed semiconductor devices
- Characterization of devices / sensors
- Training on the production and characterization technologies of semiconductor devices



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Thank you for your attention

